BYR29X-600

Ultrafast power diode Rev. 02 — 15 July 2010

Product data sheet

Product profile 1.

1.1 General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Fast switching
- Isolated plastic package
- Low forward voltage drop
- Soft recovery characteristic

1.3 Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- High frequency switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
repetitive peak reverse voltage		-	-	600	V
average forward current	square-wave pulse; $\delta = 0.5$; $I_h \le 73$ °C; see Figure 1; see Figure 2; see Figure 3	1] _	-	8	Α
non-repetitive peak forward current	$T_{j(init)}$ = 25 °C; t_p = 10 ms; sine-wave pulse	-	-	60	Α
acteristics					
forward voltage	I _F = 8 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.07	1.5	V
naracteristics					
reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/µs}$; $T_j = 25 ^{\circ}\text{C}$; see Figure 8; see Figure 7	-	60	75	ns
	repetitive peak reverse voltage average forward current non-repetitive peak forward current acteristics forward voltage	repetitive peak reverse voltage $ \begin{array}{ll} \text{repetitive peak reverse} \\ \text{voltage} \\ \text{average forward} \\ \text{current} \\ Supplement to the content to the cont$	repetitive peak reverse voltage $ \begin{array}{lll} & - & \\ & \text{average forward} \\ & \text{current} \end{array} & \begin{array}{lll} & \text{square-wave pulse; } \delta = 0.5 \ ; & \begin{array}{lll} 11 \\ - \\ & \text{T}_h \leq 73 \ ^\circ\text{C; see } \frac{\text{Figure 1;}}{\text{see } \text{Figure 2; see } \text{Figure 3}} \end{array} \\ & \text{non-repetitive peak} \\ & \text{forward current} \end{array} & \begin{array}{lll} & T_{j(\text{init})} = 25 \ ^\circ\text{C; t}_p = 10 \ \text{ms;} \\ & \text{sine-wave pulse} \end{array} & - \\ & \text{acteristics} \\ & \text{forward voltage} \end{array} & \begin{array}{lll} & I_F = 8 \ \text{A; T}_j = 150 \ ^\circ\text{C;} \\ & \text{see } \frac{\text{Figure 5}}{\text{Figure 5}} \end{array} & - \\ & \text{aracteristics} \\ & \text{reverse recovery time} \end{array} & \begin{array}{lll} & I_F = 1 \ \text{A; V}_R = 30 \ \text{V;} \\ & \text{d}_{F}/\text{d}_{t} = 100 \ \text{A/\mu s;} \\ & T_j = 25 \ ^\circ\text{C; see } \frac{\text{Figure 8;}}{\text{Figure 8;}} \end{array} $	repetitive peak reverse voltage $ \begin{array}{ccccccccccccccccccccccccccccccccccc$	repetitive peak reverse voltage $ \begin{array}{ccccccccccccccccccccccccccccccccccc$

^[1] Neglecting switching and reverse current losses



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	Α	anode	mb	K — A 001aaa020
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYR29X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	T _h ≤ 136 °C; DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; $T_h \le 73$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	[1] -	8	Α
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t_p = 25 μ s; $T_h \le 73$ °C	-	16	Α
I _{FSM}	non-repetitive peak forward	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	60	Α
	current	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	66	Α
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

[1] Neglecting switching and reverse current losses

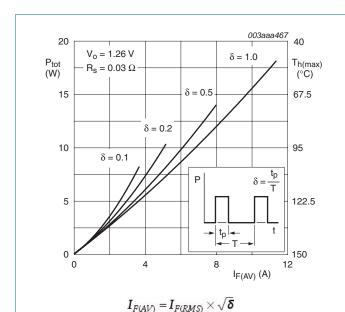
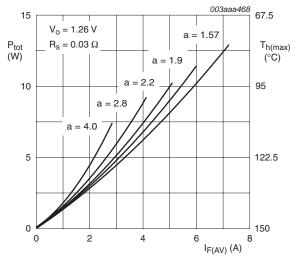
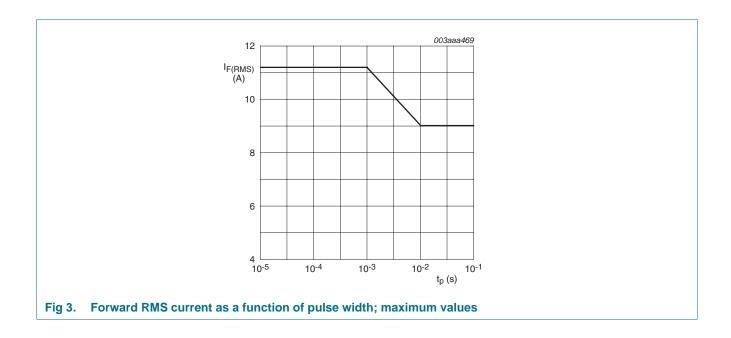


Fig 1. Forward power dissipation and permissible heatsink temperature as a function of average forward current; square waveform; maximum values



a =form factor $= I_{T(RMS)} / I_{T(AV)}$

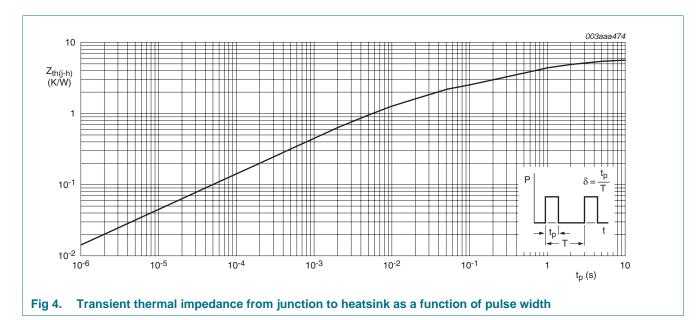
Fig 2. Forward power dissipation and permissible heatsink temperature as a function of average forward current; sinusoidal waveform; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound ; see Figure 4	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

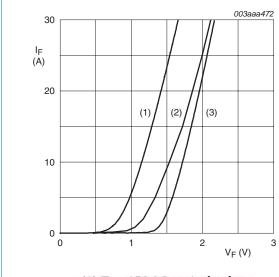
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V_{F}	forward voltage	$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.75	1.95	V
		$I_F = 8 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.07	1.5	V
		$I_F = 8 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	-	1.7	V
I _R reverse current	reverse current	$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.2	mA
		$V_R = 600 \text{ V}; T_j = 25 \text{ °C}$	-	1	10	μΑ
Dynamic ch	naracteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6; see Figure 7	-	150	200	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 8; see Figure 7	-	60	75	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 100 \text{ °C}$; see <u>Figure 9</u> ; see <u>Figure 7</u>	-	-	6	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 10	-	5	-	V

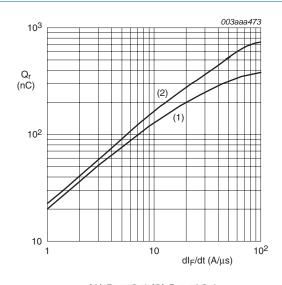


(1) $T_j = 150 \, ^{\circ}C$; typical values

(2) $T_j = 150$ °C; maximum values

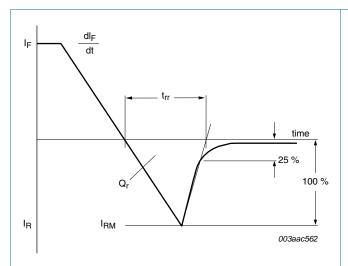
(3) $T_j = 25$ °C; maximum values





(1) $I_F = 2 \text{ A}(2) I_F = 10 \text{ A}$

Fig 6. Recovered charge as a function of rate of change of forward current



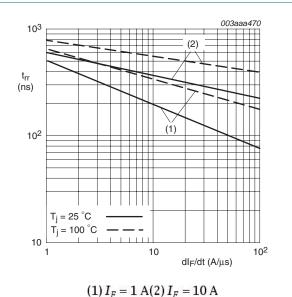
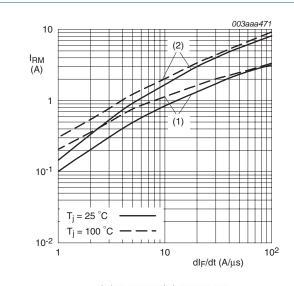


Fig 7. Reverse recovery definitions; ramp recovery

Fig 8. Reverse recovery time as a function of rate of change of forward current at indicated temperatures; maximum values



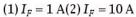


Fig 9. Peak reverse recovery current as a function of rate of change of forward current at indicated temperatures

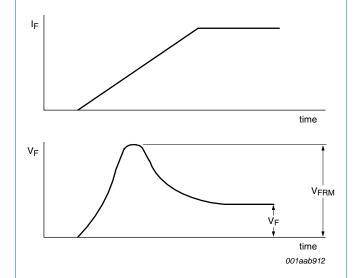


Fig 10. Forward recovery definitions

8. Package outline

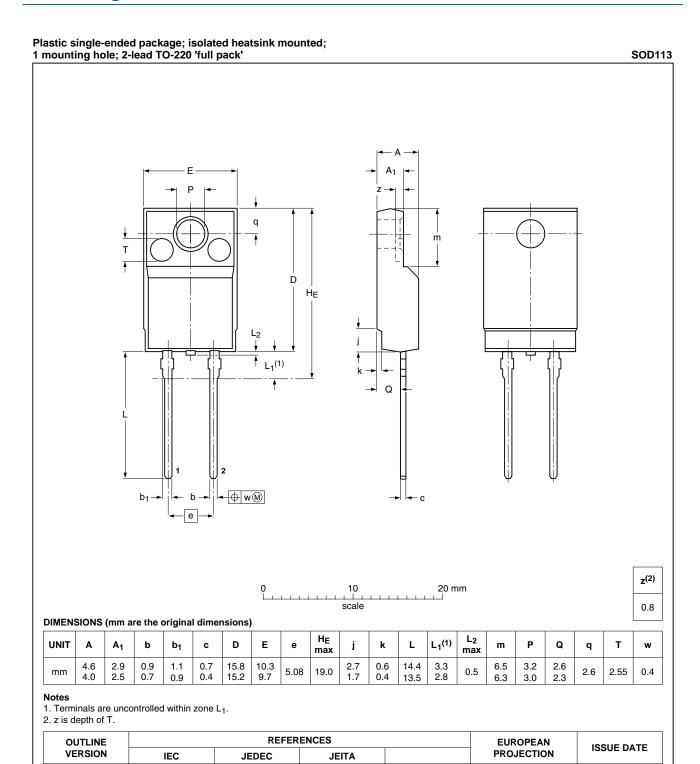


Fig 11. Package outline SOD113 (TO-220F)

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2-lead TO-220F

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SOD113

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYR29X-600 v.2	20100715	Product data sheet	-	BYR29X-600 v.1
Modifications:	 The format of this da NXP Semiconductor 	ta sheet has been redesi s.	gned to comply with the r	new identity guidelines of
	 Legal texts have been 	en adapted to the new cor	npany name where appro	opriate.
BYR29X-600 v.1 (9397 750 12006)	20030926	Product data	-	-

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10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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